SiA441DJ-T1-GE3-VB Datasheet

P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω) Typ.	I_D (A) [d]	Q_g (TYP.)
-60	0.058 at V_{GS} = -10 V	-6.5	10.1 nC
	0.070 at V_{GS} = -4.5 V	-5.1	

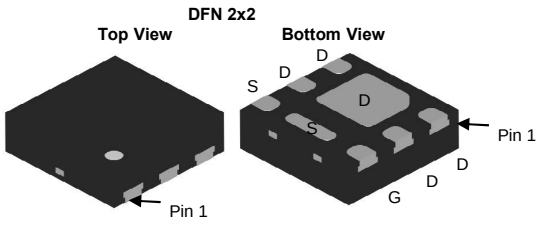
FEATURES

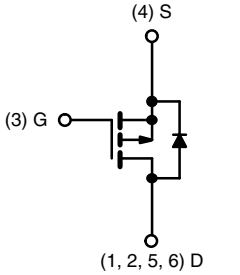
- Trench power MOSFET
- 100 % R_g and UIS tested

Pb-free
RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- Load switches
- DC/DC converter





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	-6.5	A
	T_C = 70 °C		-4.5	
	T_A = 25 °C		-3.8[a,b]	
	T_A = 70 °C		-3.1[a,b]	
Pulsed Drain Current (t = 100 µs)		I_{DM}	-20	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	-3.5	
	T_A = 25 °C		-1.7 [a,b]	
Avalanche Current	L = 0.1 mH	I_{AS}	-15	
Single-Pulse Avalanche Energy		E_{AS}	11.25	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	4.2	W
	T_C = 70 °C		2.7	
	T_A = 25 °C		2 [a,b]	
	T_A = 70 °C		1.3 [a,b]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum Junction-to-Ambient [a,c]	t ≤ 10 s	R_{thJA}	40	62.5	°C/W
Maximum Junction-to-Foot	Steady State	R_{thJF}	25	30	

Notes

a. Surface mounted on 1" x 1" FR4 board.
b. t = 10 s.
c. Maximum under steady state conditions is 110 °C/W.
d. Based on T_C = 25 °C.

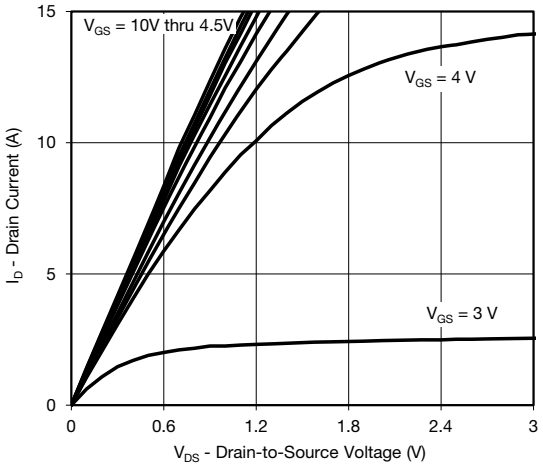
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = -250 µA	-60	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = -250 µA	-	-6.7	-	mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		-	4.3	-	
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 µA	-1	-	-3	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -60 V, V_{GS} = 0 V	-	-	-1	µA
		V_{DS} = -60 V, V_{GS} = 0 V, T_J = 55 °C	-	-	-5	
On-State Drain Current [a]	$I_{D(on)}$	V_{DS} ≥ -10 V, V_{GS} = -10 V	-30	-	-	A
Drain-Source On-State Resistance [a]	$R_{DS(on)}$	V_{GS} = -10 V, I_D = -3.5 A	-	0.058	-	Ω
		V_{GS} = -4.5 V, I_D = -2.8 A	-	0.070	-	
Forward Transconductance [a]	g_{fs}	V_{DS} = -30 V, I_D = -3.5 A	-	11	-	S
Dynamic [b]						
Input Capacitance	C_{iss}	V_{DS} = -30 V, V_{GS} = 0 V, f = 1 MHz	-	832	-	pF
Output Capacitance	C_{oss}		-	88	-	
Reverse Transfer Capacitance	C_{rss}		-	63	-	
Total Gate Charge	Q_g	V_{DS} = -30 V, V_{GS} = -10 V, I_D = -3.5 A	-	20	30	nC
		V_{DS} = -30 V, V_{GS} = -4.5 V, I_D = -3.5 A	-	10.1	15.2	
Gate-Source Charge	Q_{gs}		-	3.3	-	
Gate-Drain Charge	Q_{gd}		-	3.9	-	
Gate Resistance	R_g	f = 1 MHz	1.8	9	18	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = -30 V, R_L = 10.7 Ω I_D ≅ -2.8 A, V_{GEN} = -10 V, R_g = 1 Ω	-	8	16	ns
Rise Time	t_r		-	6	12	
Turn-Off DelayTime	$t_{d(off)}$		-	35	53	
Fall Time	t_f		-	16	24	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = -30 V, R_L = 10.7 Ω I_D ≅ -2.8 A, V_{GEN} = -4.5 V, R_g = 1 Ω	-	40	60	
Rise Time	t_r		-	28	42	
Turn-Off DelayTime	$t_{d(off)}$		-	31	47	
Fall Time	t_f		-	15	23	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I_S	T_C = 25 °C	-	-	-3.5	A
Pulse Diode Forward Current (t = 100 µs)	I_{SM}		-	-	-20	
Body Diode Voltage	V_{SD}	I_S = -2.8 A, V_{GS} = 0 V	-	-0.85	-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = -2.8 A, dI/dt = 100 A/µs, T_J = 25 °C	-	32	48	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	45	68	nC
Reverse Recovery Fall Time	t_a		-	24	-	ns
Reverse Recovery Rise Time	t_b		-	8	-	

Notes

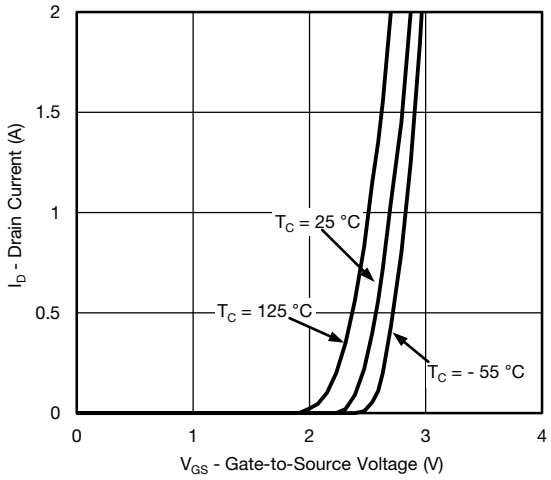
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

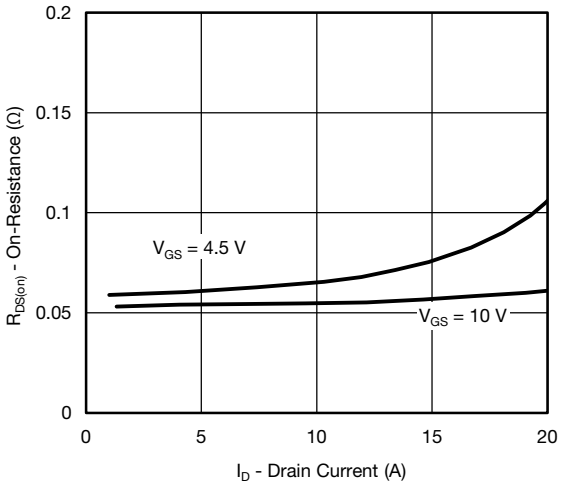
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



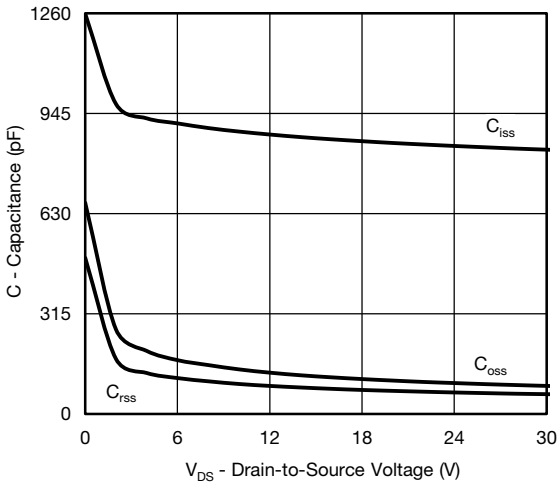
Output Characteristics



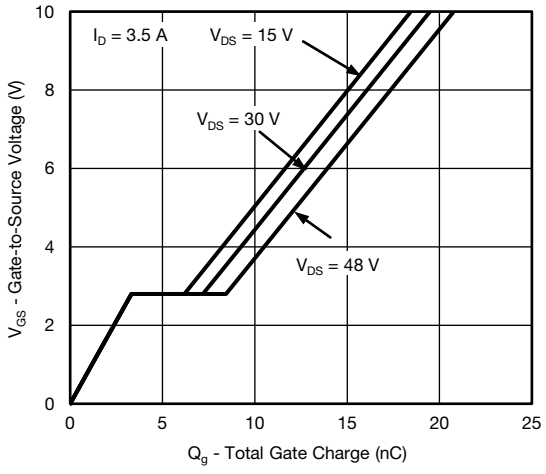
Transfer Characteristics



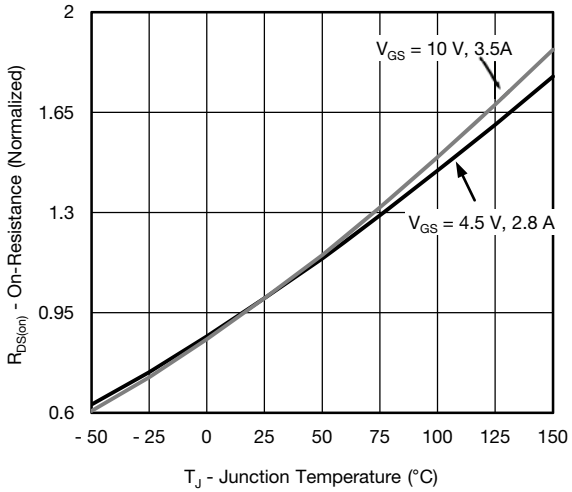
On-Resistance vs. Drain Current



Capacitance

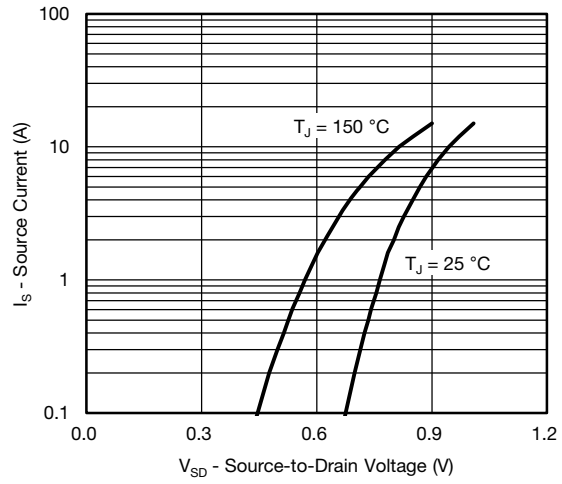


Gate Charge

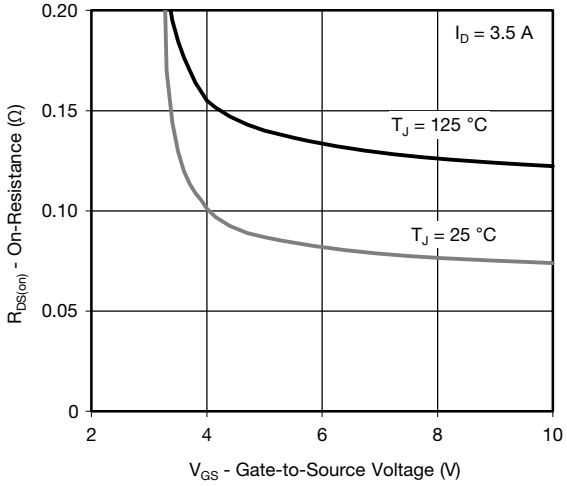


On-Resistance vs. Junction Temperature

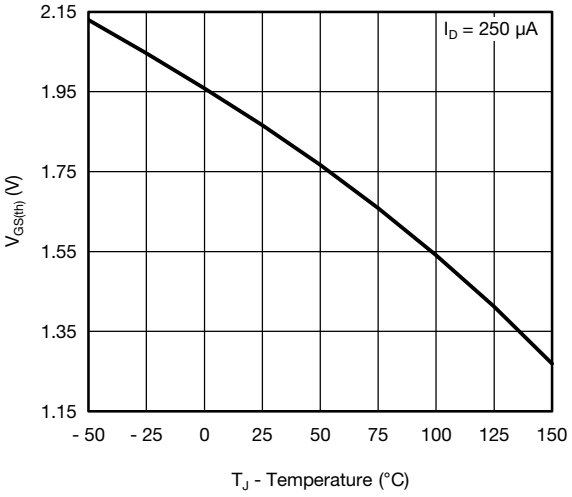
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



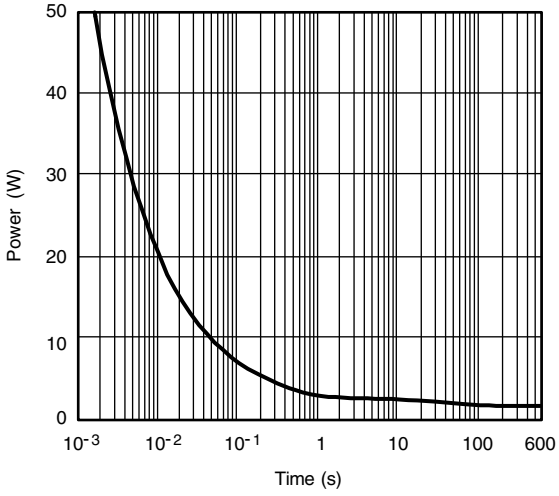
Source-Drain Diode Forward Voltage



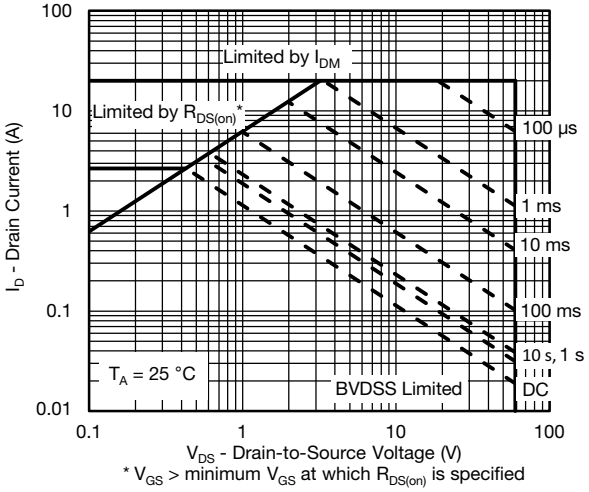
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

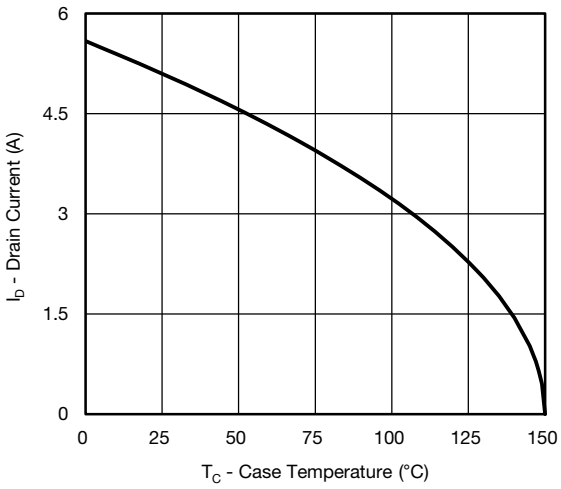


Single Pulse Power, Junction-to-Ambient

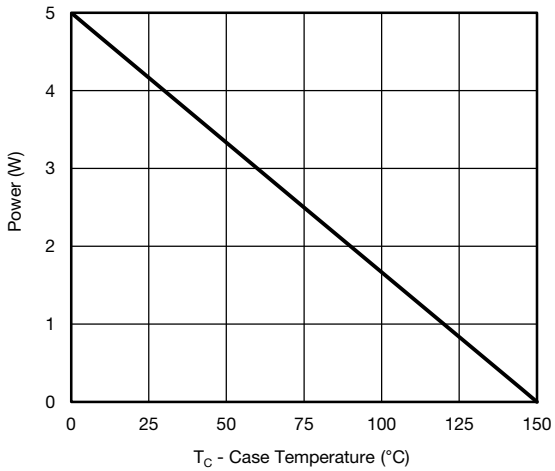


Safe Operating Area

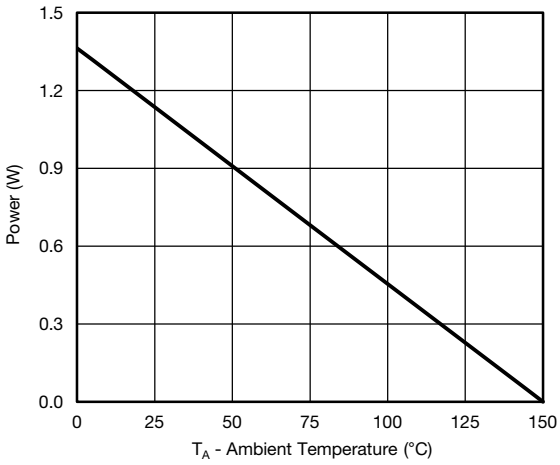
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



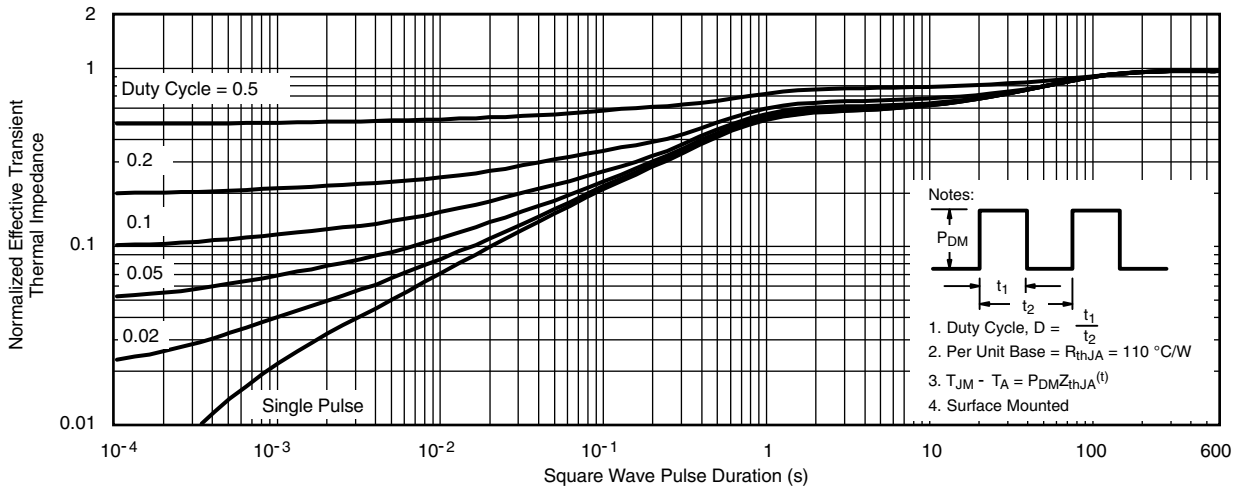
Power, Junction-to-Foot



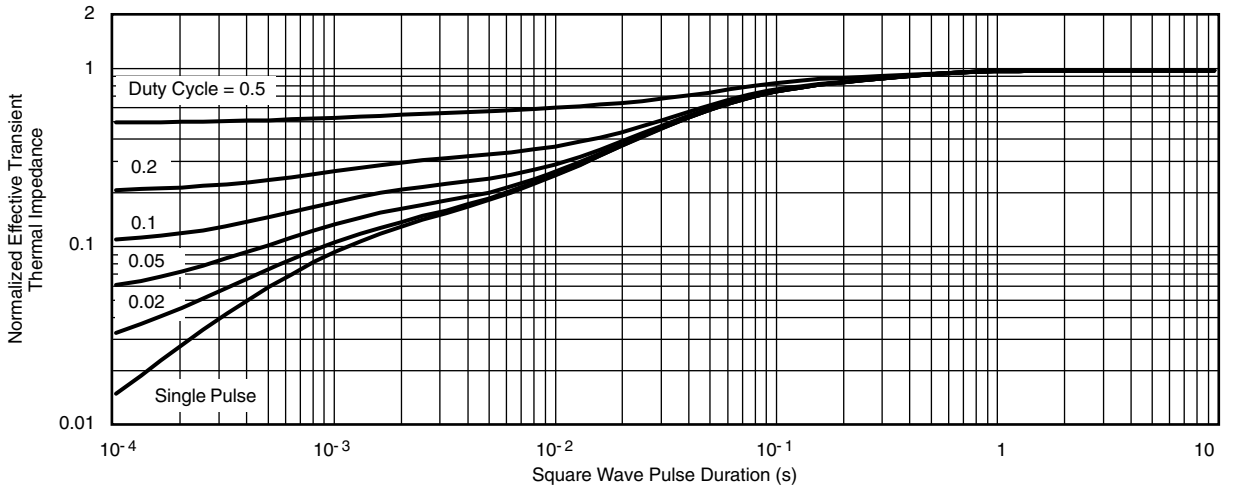
Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J\ (max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

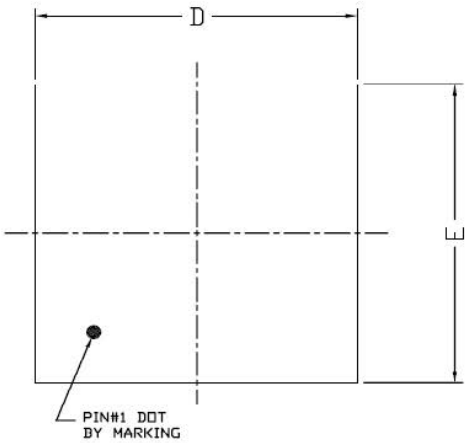


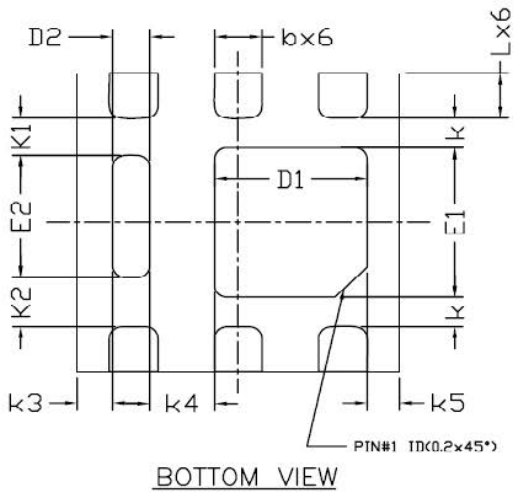
Normalized Thermal Transient Impedance, Junction-to-Ambient



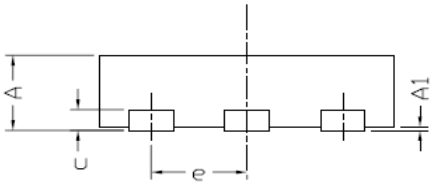
Normalized Thermal Transient Impedance, Junction-to-Foot

DFN2x2 _6L_EP1_S PACKAGE OUTLINE

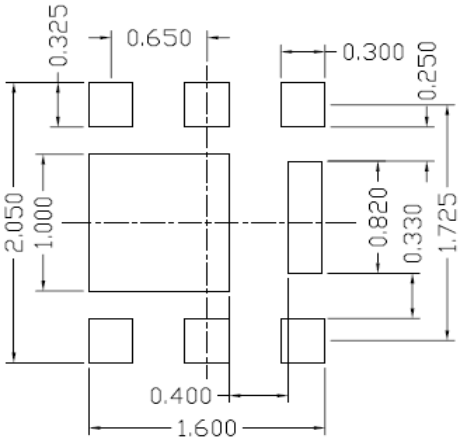




BOTTOM VIEW



RECOMMENDED LAND PATTERN

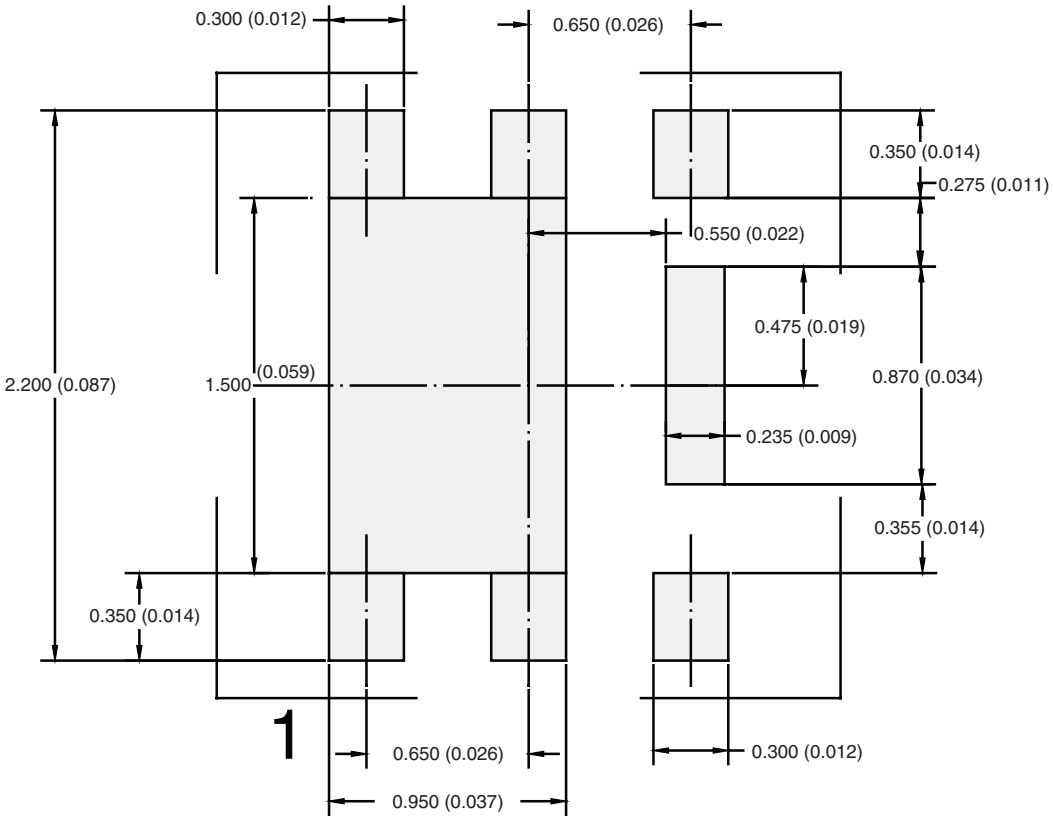


UNIT: mm

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.022	0.024
A1	0.00	——	0.05	0.000	——	0.002
b	0.25	0.30	0.35	0.010	0.012	0.014
c	0.152 REF			0.006 REF		
D	1.90	2.00	2.10	0.075	0.079	0.083
D1	0.85	0.95	1.05	0.033	0.037	0.041
D2	0.13	0.23	0.33	0.005	0.009	0.013
E	1.90	2.00	2.10	0.075	0.079	0.083
E1	0.90	1.00	1.10	0.035	0.039	0.043
E2	0.72	0.82	0.92	0.028	0.032	0.036
e	0.65 BSC			0.026 BSC		
K	0.20 BSC			0.008 BSC		
K1	0.25 BSC			0.010 BSC		
K2	0.33 BSC			0.013 BSC		
K3	0.22 BSC			0.009 BSC		
K4	0.40 BSC			0.016 BSC		
K5	0.20 BSC			0.008 BSC		
L	0.25	0.30	0.35	0.010	0.012	0.014

NOTE
1. CONTROLLING DIMENSION IS MILLIMETER.
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

RECOMMENDED PAD LAYOUT FOR DFN2X2



Dimensions in mm/(Inches)

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